THERMAL CONDUCTIVITY OF Zn_{4-x}Cd_xSb₃SOLID SOLUTIONS

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ABSTRACT

β- Zn_4Sb_3 was recently identified at the Jet Propulsion Laboratory as a new high performance p-type thermoelectric material with a maximum dimensionless thermoelectric figure of merit ZT of 1.4 at a temperature of 673K. A usual approach, used for many state-of-the-art thermoelectric materials, to further improve ZT values is to alloy β- Zn_4Sb_3 with isostructural compounds because of the expected decrease in lattice thermal conductivity. We have grown $Zn_{4-x}Cd_xSb_3$ crystals with $0.2 \le x < 1.2$ and measured their thermal conductivity from 10 to SOOK. The thermal conductivity values of $Zn_{4-x}Cd_xSb_3$ alloys are significantly lower than those measured for β- Zn_4Sb_3 and are comparable to its calculated minimum thermal conductivity. A strong atomic disorder is believed to be primarily at the origin of the very low thermal conductivity of these materials which are also fairly good electrical conductors and are therefore excellent candidates for thermoelectric applications.

INTRODUCTION

As part of a broad search for new, more efficient thermoelectric materials conducted at the Jet Propulsion Laboratory, β-Zn₄Sb₃ was recently identified as a new high performance p-type mater-ial [1,2]. β-Zn₄Sb₃ has interesting thermoelectric properties in the 473-673K temperature range and a maximum dimensionless thermoelectric figure 01' merit ZT of 1.4 was obtained at a temperature of 400°C. One of the features of β-Zn₄Sb₃ is its remarkably low thermal conductivity with a room temperature lattice thermal conductivity of 6.5 mW/cmK. Formation of solid solutions is a well known approach used for thermoelectric materials in particular 10 lower the lattice thermal conductivity and most state-of-tbc-ad thermoelectric materials arc, in fact, solid solutions. The performance of a thermoelectric mater-ial can be improved if thermal conductivity could be reduced without a strong degradation in electrical properties. We therefore started to investigate the possibility of alloying \(\beta - \text{Zn}_4 \text{Sb}_3\) with isostructural compounds and explore the potential of these alloys for thermoelectric applications. Only one compound which forms a complete series of solid solution with β-Zn₄Sb₃ has been reported in the literature: Cd₄Sb₃ [3]. As a first step to assess the usefulness of Zn_{4-x}Cd_xSb₃ solid solutions for thermoelectric applications, we have grown crystals and measured their thermal conductivity from 10 to 500K.

EXPERIMENT

 $Zn_{4-x}Cd_xSb_3$ crystals with $0.2 \le x \le 1.2$ were grown by the Bridgman gradient freeze technique. Zinc (Zn) shots (99.999% pure), cadmium (Ccl) powder shots (99.999% pure) and antimony (Sb) shots (99.999% pure) in stoichiometric ratio were loaded into carbon coated quartz

ampoules with pointed bottom. The ampoules were subsequently evacuated and scaled (10-5 Torr). They were then introduced in a vertical two-zone furnace and remained stationary during the growth. A gradient of about 50K/cm and a growth rate of about 0.7K/hour were used in the experiments. Details about the growth process can be found elsewhere [4]. Crystals of about 6 mm in diameter and up to 2 cm long were obtained by this technique. Some crystals were ground for x-ray diffractometry (XRD) analysis which showed that the samples were single phase with a structure corresponding to β -Zn₄Sb₃. Microprobe analysis (M PA) also showed that the samples were single phase and homogeneous in composition. Details about microstructure analysis techniques can be found elsewhere [4]. Changes in the Zn to Cd ratio along the grown ingots, inherent to the growth process used, were found by M PA. Samples often presented macrocracks due the phase transformation from γ -Zn₄Sb₃ to β -Zn₄Sb₃ occurring upon cooling around 765K. These two phases presumably have different coefficient of expansion, resulting in stresses during cooling and causing the cracks formation. Large grains, isolated from the ingots, were used for thermal conductivity and electrical resistivity measurements. The samples were analyzed by MPA prior to the measurements to determine their composition.

Between room temperature and 500K, the thermal conductivity of samples cut perpendicularly to the growth axis were measured by a flash diffusivity technique which has been described elsewhere [5]. The error in the measurements was estimated at about 10%. From 10 to 300K, thermal conductivity measurements was carried out by the four-probe steady-slate technique which has been described in [6]. For these measurements, samples of several mm long were cut in the shape of parallelepipeds with a heat flow along the longest axis. The error for these measurements was estimated at about 15% at room temperature and decreases at lower temperatures and is about 5% below 200K because the radiation 10 sscs, which is the main source of error, become negligible at low temperatures. The electrical resistivity was measured from 10 to 500K using the van der Pauw technique as described before [6,7].

RESULTS

The thermal conductivity of p-type $Zn_{4-x}Cd_xSb_3$ samples is shown in Fig. 1 and is compared to β - Zn_4Sb_3 and some state-of-the-art thermoelectric materials. $Zn_{4-x}Cd_xSb_3$ alloys have the lowest thermal conductivity of all the materials in the entire temperature range, The substitution of Cd atoms for Zn significantly lower the thermal conductivity in the alloys. At room temperature the thermal conductivity of β - Zn_4Sb_3 is 9 mW/cmK whereas the values for $Zn_{4-x}Cd_xSb_3$ samples range from 5.5 to 7 mW/cmK depending on the value of x. Between 10 and 300K, the thermal conductivity of the alloys is nearly temperature independent, a signature of strong phonon scattering by point defects. The phase transformation occurring at 263 K [2] does not appear to result in changes in thermal conductivity values whereas it seemed to alter the electrical resistivity values [9]. The low thermal conductivity values make these p-type materials potentially interesting for optimization of their thermoelectric properties at low temperatures.

The effect of alloy scattering on the lattice thermal conductivity of β-Zn₄Sb₃ can be evaluated using the model proposed by Callaway and von Baeyer [10]. Details of the calculation can be found in [11]. Experimental data for Zn₄Sb₃ needed for the calculations such as the Debye temperature, sound velocity and average volume per atom in the crystal can be found in [2]. The mode] also requires to determine a strain parameter for the substituted sites which was adjusted

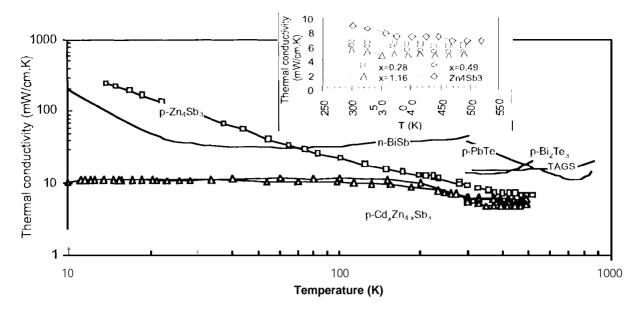


FIG. 1. Thermal conductivity vs. temperature for p-type β -Zn₄Sb₃ and p-type Zn_{4-x}Cd_xSb₃ alloys. The thermal conductivity for some state-of-the-art thermoelectric materials is also shown for comparison,

by considering the experimental lattice thermal conductivity of the alloys. They were calculated using the Wiedemann-Franz law and the measured electrical resistivity (in the order of 2 to 3.5 m Ω cm for all samples). A Lorenz number of 2.2 x10⁻⁸ V²/deg² was assumed for all samples and was chosen according to the doping level of the samples. The strain parameter (ε_{tm}) value was calculated for the Zn site by considering the lattice thermal conductivity of the Zn₂₈₄Cd_{1.16}Sb₃ sample at 300K. The best match was achieved for a value of ε_{tm} and 3. The results of the calculations are shown in Fig. 2 and compared to several experimental values. A maximum decrease of about 30'% in lattice thermal conductivity is predicted for a Zn₂Cd₂Sb₃ composition compared to β -Zn₄Sb₃. For x=0.5, a 25% decrease is already obtained. in the light of these results, it seems that efforts should primarily focus on the optimization of the electrical properties of Zn_{4-x}Cd_xSb₃ solid solutions with 0.5≤x≤1to assess if any improvement in the thermoelectric performance can be obtained for the alloys.

Using the same formalism, we have also calculated the impact of substituting As for Sb in hypothetical $Zn_4Sb_{3-x}As_y$ solid solutions. We have assumed the same strain parameter of ε_{tm} =-43 for the calculations, The results, shown in Fig 2., indicate that the reduction in lattice thermal conductivity is smaller than for $Zn_{4-x}Cd_xSb_3$ alloys, essentially because of the smaller number of sites substituted considering that mass and volume fluctuations are basically the same between Zn and Cd, and Sb and As. Fig 2. also shows the calculated lattice thermal conductivity when substitution occurs on both sites. The 10wcs1 calculated lattice thermal conductivity is nearly 4 mW/cmK for 50% of Cd and As substituted for Zn and Sb, respectively.

We have calculated the lattice thermal conductivity as a function of the temperature using the Wiedemann-Franz law using again a Lorenz number of 2.2 x 10⁻⁸ V²/deg². The results are shown in Fig 3. The lattice thermal conductivity are low and approaches glass-like thermal properties. 1 t was interesting to compare the experimental values to the calculated minimum thermal conductivity, a concept first proposed by Slack [12] and later developed by Cahillet al. based on

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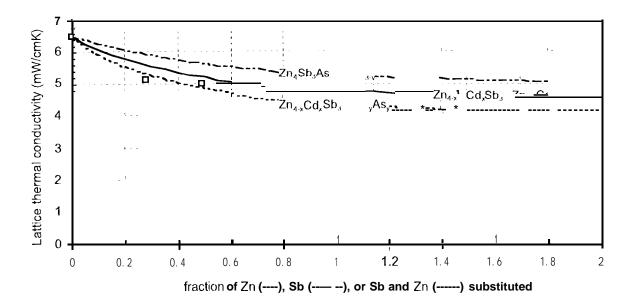


FIG. 2. Ei'feel of alloy scattering on the room temperature lattice thermal conductivity of β-Zn₄Sb₃. The values were calculated as a function of the fraction x for Zn_{4-x}Cd_xSb₃ alloys (x_{max} = 2) and y in Zn₄Sb_{3-y}As_y alloys (y_{max} = 1.5). For Zn_{4-x}Cd_xSb_{3-y}As_y alloys, the calculated values reflect a scaling of y_{max} to a value of 2. The symbol denotes experimental data for Zn_{4-x}Cd_xSb₃ alloys.

a model due to Einstein [1 3]. The minimum thermal conductivity is expressed as a sum of three Debye integrals by [1 3]:

$$\lambda_{\min} = \left(\frac{\pi}{6}\right)^{1/3} k_{\rm B} n^{2/3} \sum_{i} v_{i} \left(\frac{T}{\theta_{i}}\right)^{2} \int_{0}^{\theta_{i}/T} \frac{x^{3} e^{x}}{(e^{x}-1)^{2}} dx$$
 (1)

The sum is taken over the three sound modes (two transversal and one longitudinal) with speeds of sound vi. k_B is the Boltzmann's constant, n the atomic density, T the temperature in K and $\theta_i = vi \, (h/2\pi k_B) \, (6\pi^2 n)^{1/3}$. We calculated the minimum thermal conductivity for β -Zn₄Sb₃ using the speed of sound and atomic density values in [2], The results are shown in Fig. 3. The minimum lattice thermal conductivity for β -Zn₄Sb₃ at room temperature is 4.2 mW/cmK which is only slightly lower than the experimental value of 6.5 mW/cmK. For the Zn_{2.84}Cd_{1.16}Sb₃ alloy, the experimental value is close to the calculated minimum value at room temperature and is lower for higher temperatures reaching a minimum of 2.5 mW/cmK at 500K. At 100K, the lattice thermal conductivity of the alloy is about three times larger than the calculated minimum. Glass-like thermal conductivity have been observed in highly disordered materials and crystals containing loosely bonded atoms such as filled skutterudite materials [14-17]. In contrast, simple monoatomic substitution cannot lead to glass-like thermal conductivity. Therefore, it is remarkable that Zn_{4-x}Cd_xSb₃ materials possess thermal conductivity similar to glass-like materials which we believe is due to a highly disordered structure. Indeed, the crystal structure of these materials requires disorder on one of the Sb sites for the stoichiometry [1 8]. in addition, Auger

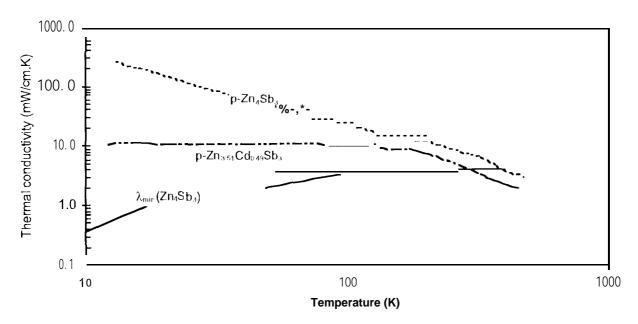


FIG. 3. Lattice thermal conductivity vs. temperature for p-type β -Zn₄Sb₃ and p-type Zn_{3.51}Cd_{0.49}Sb₃ alloy. The solid line is the calculated lattice thermal conductivity for β -Zn₄Sb₃ using equation (1),

electron spectroscopy performed on β -Zn₄Sb₃ crystals revealed localized deviations from the exact stoichiometry [19] which suggests the presence of structural defects such as vacancies which can produce strong phonon scattering as it has been observed, for example, in In₂Te₃, [20]. Further evidence of the atomic disorder for Zn_{4-x}Cd_xSb₃ materials was given by optical absorption and reflection measurements performed on β -Zn₄Sb₃ materials crystals [19].

CONCLUSIONS

We have measured the thermal conductivity of $Zn_{4-x}Cd_xSb_3$ materials with $0.2x \le 1.2$ between 10 and 500K. The results show that these materials exhibit very low thermal conductivity comparable to the calculated minimum thermal conductivity of β - Zn_4Sb_3 around room temperature. It is believed that a high atomic structural disorder is essentially responsible for these low values. Most of the materials having glass-like thermal conductivity are poor electrical conductors and therefore are of little interest for thermoelectric applications. in contrast, $Zn_{4-x}Cd_xSb_3$ materials are fairly good electrical conductors with electrical resistivity in the 2 to 3.5 m Ω cm range anti appear to be excellent candidates for thermoelectric applications. Future efforts will focus on the investigations and optimization of their electrical properties.

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